

### Description

#### Features

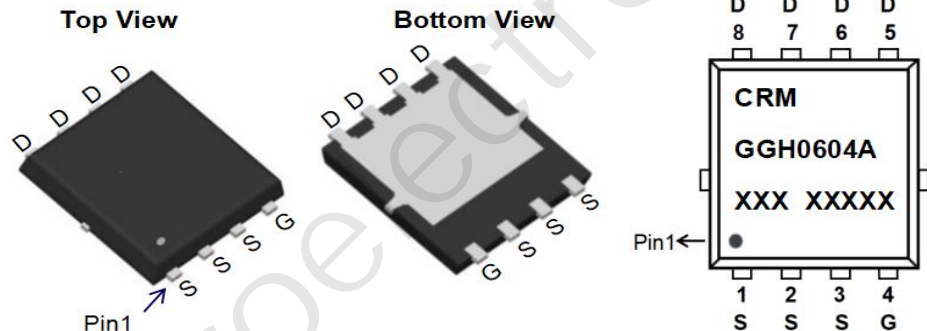
- 60V, 90A
- $R_{DS(ON)}$  Typ = 4.2mΩ @  $V_{GS} = 10V$
- Advanced Split Gate Trench Technology
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- 100% UIS TESTED!
- 100%  $\Delta V_{ds}$  TESTED!



Schematic Diagram

#### Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

#### Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMGGH0604A	CRMGGH0604A	PDFN5x6-8L	TAPING	13"	5000	60000

#### Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
$V_{DS}$	Drain-to-Source Voltage	60	V
$V_{GS}$	Gate-to-Source Voltage	±20	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	90
		$T_C = 100^\circ\text{C}$	54
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	360	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	121	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	78
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.6	°C/W
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	°C

### Electrical Characteristics ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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#### Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	60	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA

#### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	2.4	2.8	3.6	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance <sup>(3)</sup>	$V_{GS} = 10\text{V}, I_D = 30\text{A}$	-	4.2	5.5	mΩ

#### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 30\text{V},$ $f = 1\text{MHz}$	-	1563	-	pF
$C_{oss}$	Output Capacitance		-	580	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	14	-	pF
$Q_g$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 30\text{V}, I_D = 20\text{A}$	-	29	-	nC
$Q_{gs}$	Gate Source Charge		-	8.3	-	nC
$Q_{gd}$	Gate Drain("Miller") Charge		-	5.8	-	nC

#### Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 30\text{V}$ $I_D = 20\text{A}, R_{GEN} = 4.5\Omega$	-	10	-	ns
$t_r$	Turn-On Rise Time		-	28	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	20	-	ns
$t_f$	Turn-Off Fall Time		-	95	-	ns

#### Drain-Source Diode Characteristics and Max Ratings

$I_S$	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}, I_S = 30\text{A}$	-	-	90	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	360	A
$V_{SD}$	Drain to Source Diode Forward Voltage		-	-	1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time		-	31	-	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	19	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 30\text{V}$ ,  $V_G = 10\text{V}$ ,  $R_G = 25\Omega$ ,  $L = 0.5\text{mH}$ ,  $I_{AS} = 22\text{A}$
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .

## Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

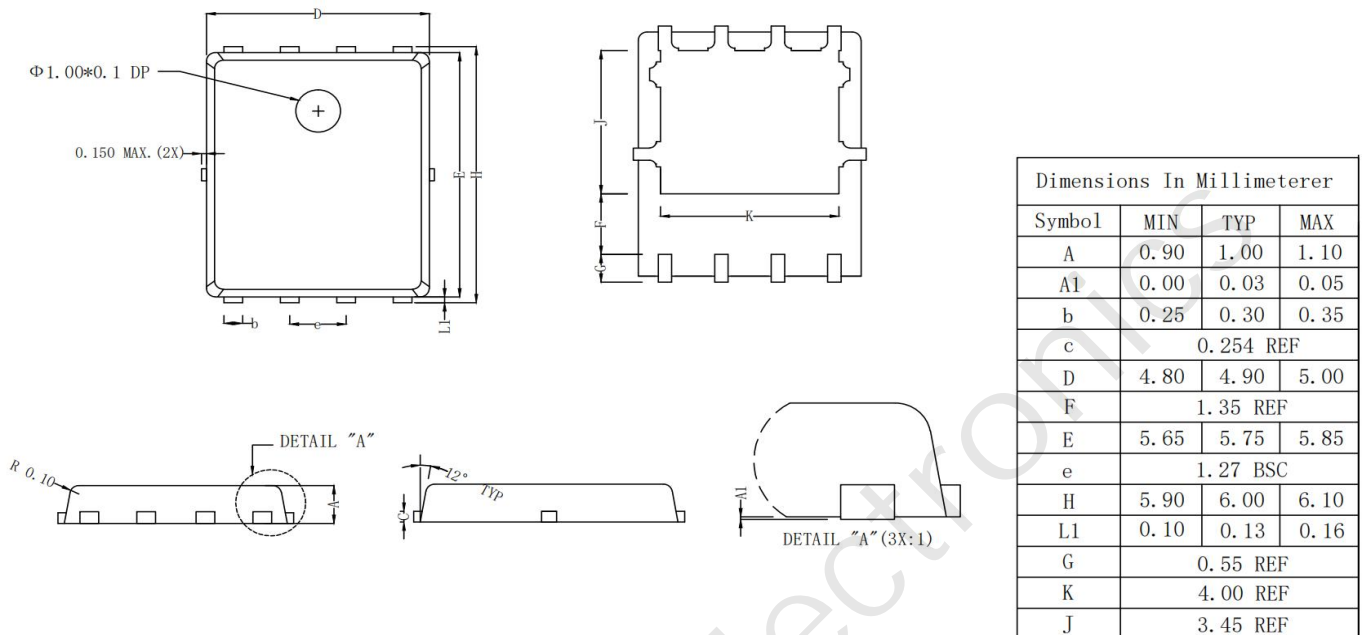


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform



Figure 4: Diode Recovery Test Circuit & Waveform

### Package Mechanical Data(PDFN5x6-8L)




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### Contact information

For more information, please visit: <http://www.crm-semi.tech>

For sales information, please send an email to: [sales@crm-semi.com](mailto:sales@crm-semi.com)